

### **N-Channel 60V MOSFET**

#### E060N035CL1

| V <sub>DS</sub> (V) | $R_{DS(on),max}$ (m $\Omega$ ) | I <sub>D</sub> (A) |  |
|---------------------|--------------------------------|--------------------|--|
| 60V                 | 35 @ V <sub>GS</sub> = 10V     | 21                 |  |

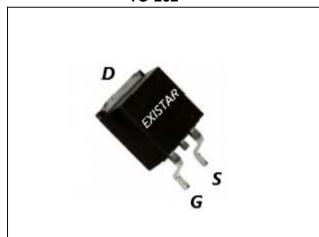
#### **Features**

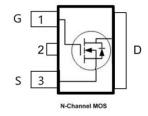
- Low R<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

## **Applications**

- DC/DC conversion
- Power switch

#### TO-252







## **Package And Ordering Information**

| Ordering code | Package | Marking     |  |
|---------------|---------|-------------|--|
| E060N035CL1   | TO-252  | E060N035CL1 |  |

## **Ordering Information**

| Package | Units/ Reel | Reels/ Inner Box | Units/ Inner Box |
|---------|-------------|------------------|------------------|
| TO-252  | 2500        | 2                | 5000             |



**Key Performance Parameters** 

| Parameter              | Value | Unit |
|------------------------|-------|------|
| VDS, min @ Tj(max)     | 60    | V    |
| ID, pulse              | 84    | А    |
| RDS(ON), max @ VGS=10V | 35    | mΩ   |
| Qg                     | 32.5  | nC   |

Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted

| Parameter  | Symbol                            | Limit            | Unit |   |
|--|-----------------------------------|------------------|------|---|
| Drain-source voltage                             | V <sub>DS</sub>                   | 60               |      |   |
| Gate-source voltage                              | V <sub>GS</sub>                   | ±20              | V    |   |
|  | T <sub>C</sub> =25°C              |                  | 21   |   |
| Continuous drain current                         | T <sub>C</sub> =100°C             | - I <sub>D</sub> | 14.9 |   |
| Pulsed drain current                             | I <sub>D,pulse</sub>              | 84               | А    |   |
| Avalanche energy, single pulse                   | E <sub>AS</sub>                   | 256              | mJ   |   |
| Down discipation                                 | Tc=25°C                           |                  | 33   |   |
| Power dissipation                                | T <sub>A</sub> =25°C              | P <sub>D</sub>   | -    | W |
| Operating junction and storage temperature range | T <sub>J</sub> , T <sub>stg</sub> | -55 To 175       | °C   |   |

#### **Thermal Characteristics**

| Parameter                               |              | Symbol           | Max. | Uni<br>t |
|---|--------------|------------------|------|----------|
| Thermal resistance, junction-to-case    | Steady state | R <sub>eJC</sub> | 4.5  |          |
| Thermal resistance, junction-to-ambient | Steady state | Reja             | -    | °C/W     |

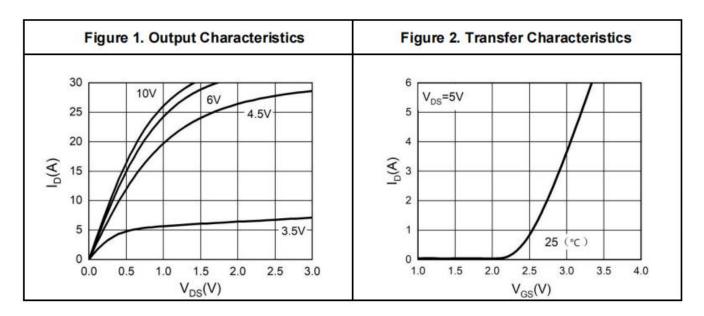
Electrical Characteristics at Tj=25°C unless otherwise specified

| Parameter                         | Symbol               | Min. | Тур. | Max. | Unit | Test conditions   |  |
|-----------------------------------|----------------------|------|------|------|------|---|--|
|                                   | Static               |      |      |      |      |   |  |
| Drain to source breakdown voltage | V <sub>(BR)DSS</sub> | 60   |      |      | V    | V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA                |  |
| Gate-source threshold voltage     | V <sub>G</sub> s(th) | 1    |      | 2.5  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA |  |
| Gate-body leakage                 | I <sub>GSS</sub>     |      |      | ±100 | nA   | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V              |  |
| Zero gate voltage drain current   | I <sub>DSS</sub>     |      |      | 1    | μA   | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V               |  |
| Drain-source on-resistance        | Ros(on)              |      | 26.4 | 35   | mΩ   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A               |  |
| Drain-source on-resistance        | Ros(on)              |      | 32.4 | 43   | mΩ   | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A               |  |
| Forward transconductance          | gfs                  |      | 14.6 |      | S    | V <sub>DS</sub> = 5 V, I <sub>D</sub> =10 A                 |  |

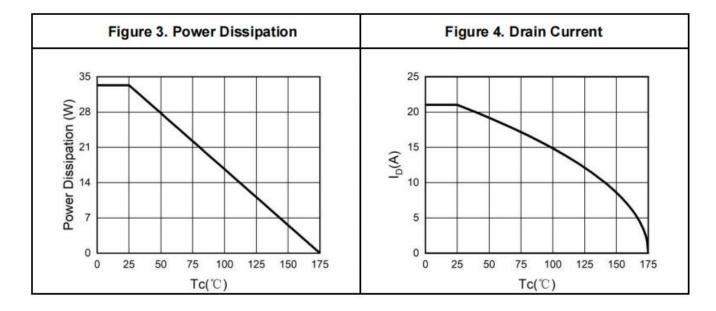


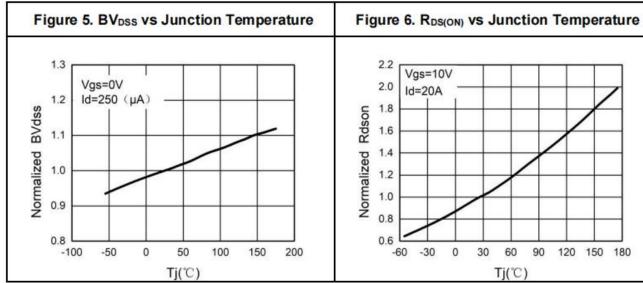
| Gate resistance              | Rg                  |  | 1.2    |     | Ω   | f=1MHz  |
|------------------------------|---------------------|--|--------|-----|-----|---|
| Gate Charge                  |                     |  |        |     |     |   |
| Total gate charge            | Qg                  |  | 32.5   |     |     |   |
| Gate-source charge           | Qgs                 |  | 3.36   |     | nC  | V <sub>DS</sub> = 30 V, I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V |
| Gate-drain charge            | Qgd                 |  | 6.4    |     |     |   |
|                              |                     |  | ynamic | ;   |     |   |
| Turn-on delay time           | $t_{d(on)}$         |  | 12.7   |     |     |   |
| Rise time                    | tr                  |  | 2.6    |     |     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V,                       |
| Turn-off delay time          | $t_{\text{d(off)}}$ |  | 27.2   |     | ns  | $R_L = 3 \Omega$ , $R_{GEN} = 3 \Omega$                               |
| Fall time                    | t <sub>f</sub>      |  | 3.2    |     | 113 |   |
| Input capacitance            | C <sub>iss</sub>    |  | 1052   |     |     |   |
| Output capacitance           | C <sub>oss</sub>    |  | 533    |     |     | V <sub>DS</sub> =30 V, V <sub>GS</sub> = 0 V, f = 1.0MHz              |
| Reverse transfer capacitance | C <sub>rss</sub>    |  | 456    |     | pF  |   |
| Body Diode                   |                     |  |        |     |     |   |
| Diode forward voltage        | $V_{\text{SD}}$     |  |        | 1.2 | V   | V <sub>GS</sub> = 0 V, I <sub>F</sub> = 10 A                          |
| Reverse recovery time        | t <sub>rr</sub>     |  | 19.5   |     | ns  | 1 40 4 4:/44 400 4/   |
| Reverse recovery charge      | Qrr                 |  | 15.8   |     | nC  | Is=10 A, di/dt = 100 A/µs   |

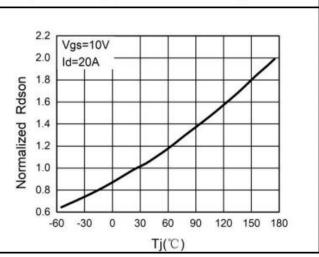
## **Electrical Characteristics Diagrams**

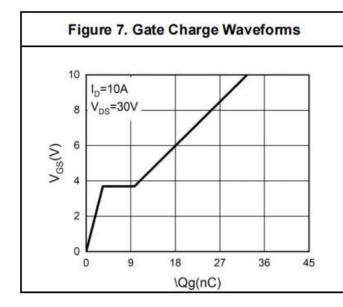


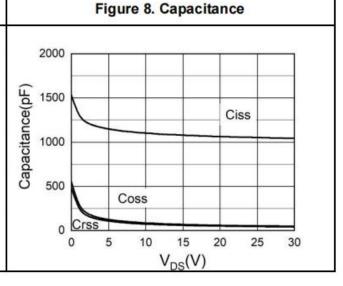




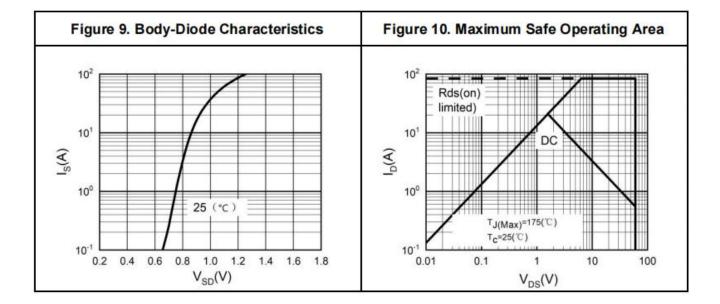






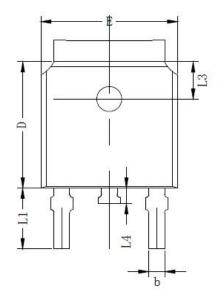


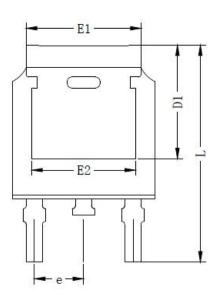






# **Package Outline Dimensions**





| SYMBOL | MIN      | NDM         | MAX   |  |  |
|--------|----------|-------------|-------|--|--|
| А      | 2.10     | 2,30        | 2.50  |  |  |
| A1     | 0.97     | 1.07        | 1.17  |  |  |
| A2     | 0.00     | -           | 0.12  |  |  |
| b      | 0.66     | 0.76        | 0.86  |  |  |
| C      | 0.45     | 0.51        | 0.60  |  |  |
| D      | 5.90     | 6.10        | 6,30  |  |  |
| D1     | 5.10     | 5,30        | 5,45  |  |  |
| E      | 6.40     | 6.60        | 6.80  |  |  |
| E1     | 5.10     | 5.33        | 5.45  |  |  |
| E2     | 4.63     | 4.83        | 5.03  |  |  |
| L      | 9,90     | 10.10       | 10,30 |  |  |
| L1     | 2.74     | 2.94        | 3.14  |  |  |
| L2     | 1.40     | 1.50        | 1.70  |  |  |
| L3     | 1.65     | 1.80        | 1.95  |  |  |
| L4     | 0,60     | 0,80        | 1.00  |  |  |
| е      | 2,286BSC |             |       |  |  |
| θ      | 5°       | 7°          | 10°   |  |  |
| θ 1    | 0°       | <del></del> | 3°    |  |  |



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